



#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max Tc = +25°C
	5.0mΩ @ V <sub>GS</sub> = 10V	87A
30V	7.4mΩ @ V <sub>GS</sub> = 4.5V	71A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

#### **Features and Benefits**

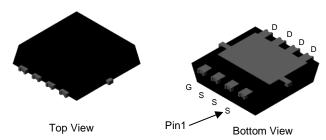
- Low Rds(ON) ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN39M1LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

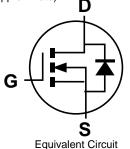
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)

Weight: 0.072 grams (Approximate)



PowerDI3333-8/SWP (Type UX)



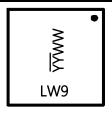
### **Ordering Information** (Note 4)

Part Number	Package	Packing		
Part Number	Package	Qty.	Carrier	
DMN39M1LFVWQ-7	PowerDI3333-8/SWP (Type UX)	2,000	Tape & Reel	
DMN39M1LFVWQ-13	PowerDI3333-8/SWP (Type UX)	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



LW9 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 24 = 2024)

WW = Week Code (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		ΙD	87 69	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	329	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	2.1	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Ism	329	Α	
Avalanche Current, L = 0.1mH (Note 8)	las	38	Α	
Avalanche Energy, L = 0.1mH (Note 8)	Eas	72	mJ	

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	96	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	46	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θ</sub> JC	2.2	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

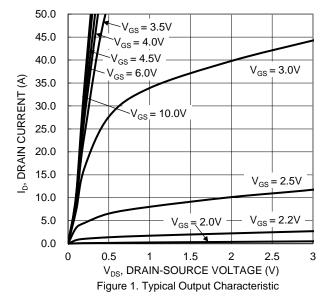
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	1	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Dagger	_	3.3	5.0	mΩ	$V_{GS} = 10V, I_{D} = 30A$	
Static Dialii-Source Off-Resistance	Rds(on)	_	5.7	7.4		$V_{GS} = 4.5V, I_{D} = 15A$	
Diode Forward Voltage	VsD	_	0.7	1.2	V	$V_{GS} = 0V$ , $I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	2387	_	рF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	292		рF		
Reverse Transfer Capacitance	Crss	_	208	_	рF		
Gate Resistance	Rg	_	2.4	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	19	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	40	_	nC	\/ - 45\/   - 45A	
Gate-Source Charge	Qgs	_	7.8	_	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 15A	
Gate-Drain Charge	$Q_{gd}$	_	5.6	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.3	_	ns		
Turn-On Rise Time	t <sub>R</sub>		3.8	_	ns	$V_{DD}$ = 15V, $V_{GS}$ = 10V, $R_{G}$ = 3.3 $\Omega$ , $I_{D}$ = 15A	
Turn-Off Delay Time	tD(OFF)	_	39	_	ns		
Turn-Off Fall Time	tF	_	11	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	20	_	ns	1 454 454 4004	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	8.9	.9 — nC		l <sub>F</sub> = 15A, di/dt = 100A/μs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J} = +25^{\circ}C$ .
- Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.





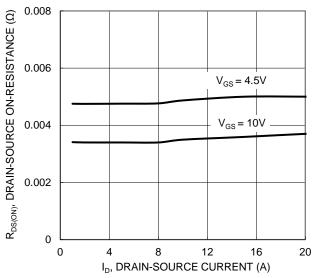


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

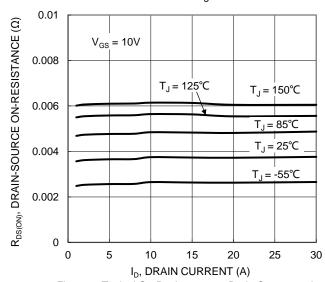
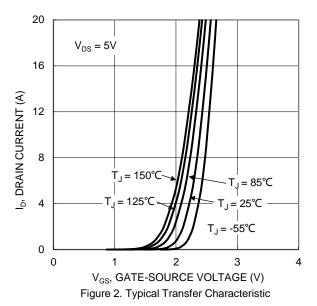
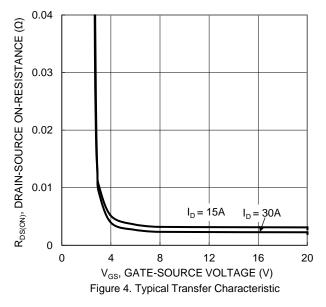


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





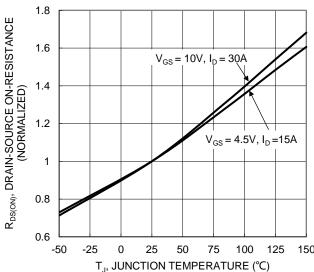


Figure 6. On-Resistance Variation with Temperature





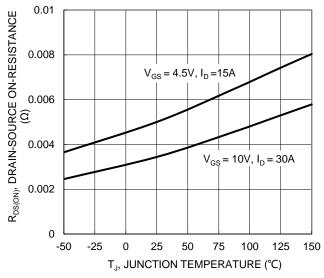


Figure 7. On-Resistance Variation with Temperature

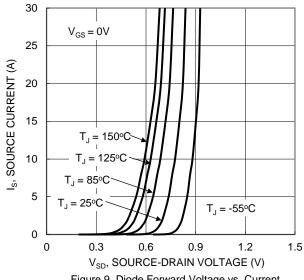


Figure 9. Diode Forward Voltage vs. Current

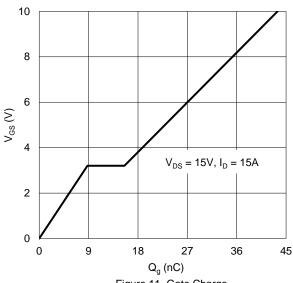


Figure 11. Gate Charge

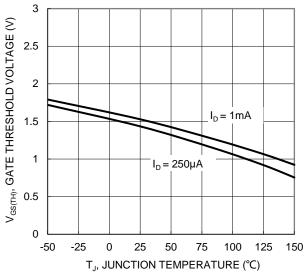
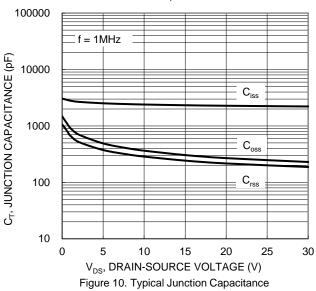


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000  $R_{DS(ON)}$ 100 ID, DRAIN CURRENT (A)  $= 10 \mu s$ 10  $P_{W} = 100 \mu s$ T<sub>J(Max)</sub> = 150°C  $T_{C} = 25^{\circ}C$ Single Pulse = 100 ms**DUT** on Infinite DC Heatsink  $V_{GS} = 10V$ 0.1 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



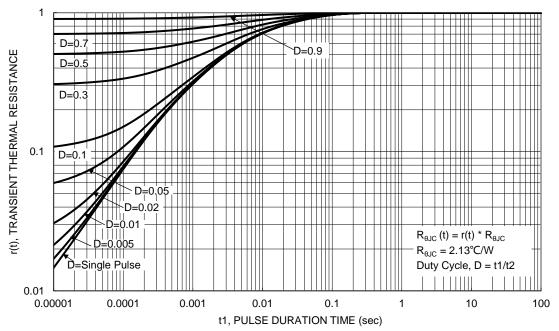


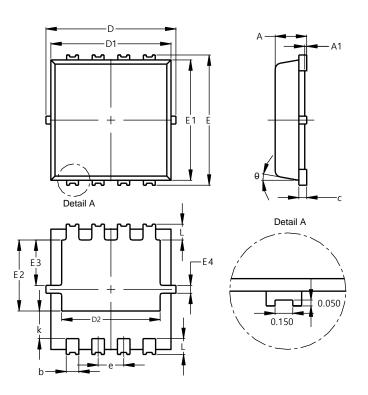
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8/SWP (Type UX)

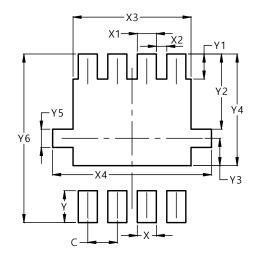


PowerDI3333-8/SWP						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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